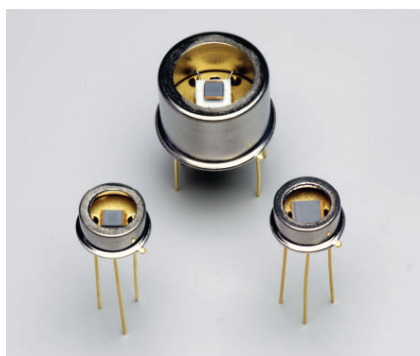


PbSe photoconductive detectors

NEW

P9696 series

P3207-08



Infrared detectors with fast response and high sensitivity in 5 μm wavelength band

Compared to other detectors used in the same wavelength regions, PbSe photoconductive detectors have faster response and can operate at room temperature, making them widely used in gas analyzers, etc. Cooling these detectors increases the sensitivity and improves the S/N. So cooled type PbSe photoconductive detectors are widely used in high-precision photometry such as for analytical instruments.

Features

- High-speed response
- Room temperature type and TE-cooled type available
- Lower temperature detection limit: approx. 50 °C
- With bandpass filter: P3207-08

Applications

- Gas analyzer (CH₄, CO, CO₂)
- Radiation thermometer
- Flame detector
- Film thickness gauge

Accessories (options)

- Heatsink for one-stage TE-cooled type **A3179**
- Heatsink for two-stage TE-cooled type **A3179-01**
- Temperature controller for TE-cooled type **C1103-04**
- Amplifier for PbS/PbSe photoconductive detector **C3757-02**
- Infrared detector module with preamp Non-cooled type **P4245**
Cooled type **P4639**

Specifications / Absolute maximum ratings

Type no.	Dimensional outline*1	Package	Cooling	Photosensitive area (mm)	Absolute maximum ratings							
					Thermistor power dissipation*2 (mW)	TE-cooler voltage consumption (V)	TE-cooler current consumption (A)	Incident light level Pin (W/cm ²)	Supply voltage Vs (V)	Operating temperature Topr (°C)	Storage temperature Tstg (°C)	Soldering conditions
P9696-02	(1)/S	TO-5	Non-cooled	2 × 2	-	-	-	1 × 10 ⁻³	100	-30 to +50	-55 to +60	260 °C or less, within 10 seconds
P9696-03				3 × 3								
P3207-08	(2)/S	TO-5*4 (with filter)		2 × 2								
P9696-102	(3)/S	TO-8	One-stage TE-cooled	2 × 2	0.2	0.85	1.5					
P9696-103			3 × 3									
P9696-202	(4)/S	TO-8	Two-stage TE-cooled	2 × 2	0.95	1.0						
P9696-203			3 × 3									

*1: S=Sapphire glass

*2: Thermistor recommended power dissipation=0.03 mW max.

*3: Voltage applied to a PbSe detector through a load resistor

*4: Half width=140 nm

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

Electrical and optical characteristics (Typ., unless otherwise noted)

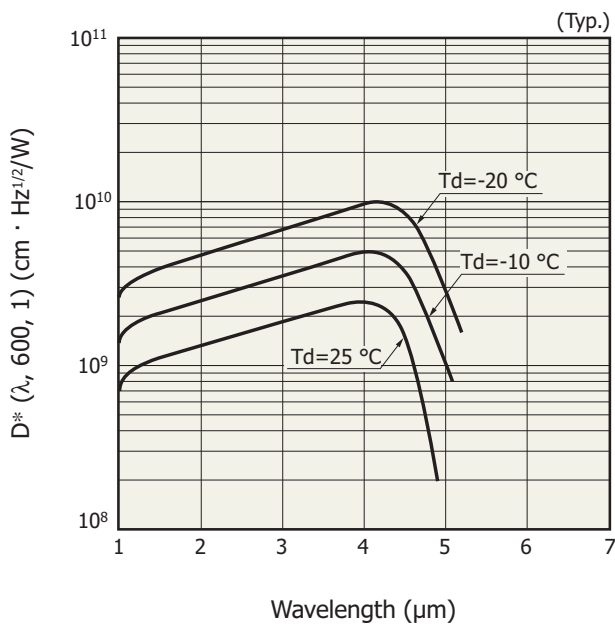
Type no.	Measurement condition	Peak sensitivity wavelength λ_p (μm)	Cut-off wavelength λ_c (μm)	Photosensitivity* ⁴ S $\lambda = \lambda_p$ $V_s = 15\text{ V}$		Detectivity D^*			Rise time t_r 0 to 63%		Thermistor resistance $T = 25\text{ }^\circ\text{C}$ (k Ω)	Thermistor B constant $T = -10\text{ to } 25\text{ }^\circ\text{C}$	Dark resistance R_d (M Ω)
	Element temperature T_d ($^\circ\text{C}$)			Min. (V/W)	Typ. (V/W)	(500, 600, 1)		(λ_p , 600, 1)	Typ. (μs)	Max. (μs)			
	($^\circ\text{C}$)	(μm)	(μm)	(V/W)	(V/W)	($\text{cm} \cdot \text{Hz}^{1/2}/\text{W}$)	($\text{cm} \cdot \text{Hz}^{1/2}/\text{W}$)	($\text{cm} \cdot \text{Hz}^{1/2}/\text{W}$)	(μs)	(μs)	(k Ω)	(M Ω)	
P9696-02	25	4.0	4.8	1.5×10^3	3×10^3	1×10^8	2.5×10^8	2.5×10^9	8	10	-	3300	0.1 to 3
P9696-03				6.7×10^2	1.3×10^3								
P3207-08* ⁵				7.8×10^2	1.5×10^3								
P9696-102	-10	4.1	5.1	5.6×10^3	7.5×10^3	2.5×10^8	5×10^8	5×10^9	10	20	9.0	3300	0.5 to 10
P9696-103				2.5×10^3	3.3×10^3								
P9696-202	-20	4.2	5.2	6.7×10^3	1×10^4	5×10^8	1×10^9	1×10^{10}	10	20	9.0	3300	0.5 to 10
P9696-203				3×10^3	4.7×10^3								

*4: Chopping frequency=600 Hz, load resistance=nearly equal to detector dark resistance

*5: Half width=140 nm

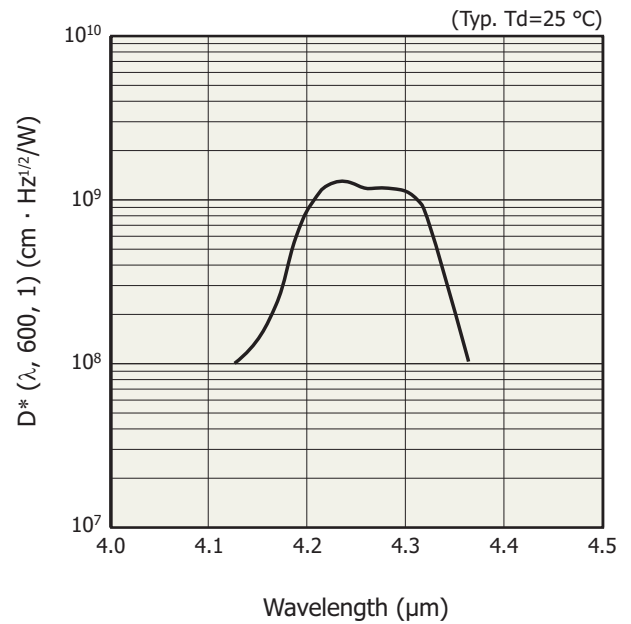
Spectral response

P9696 series



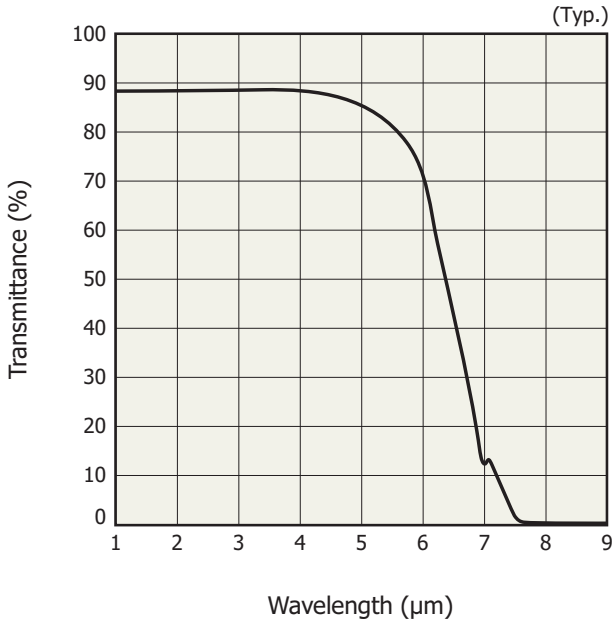
KIRD80342EF

P3207-08



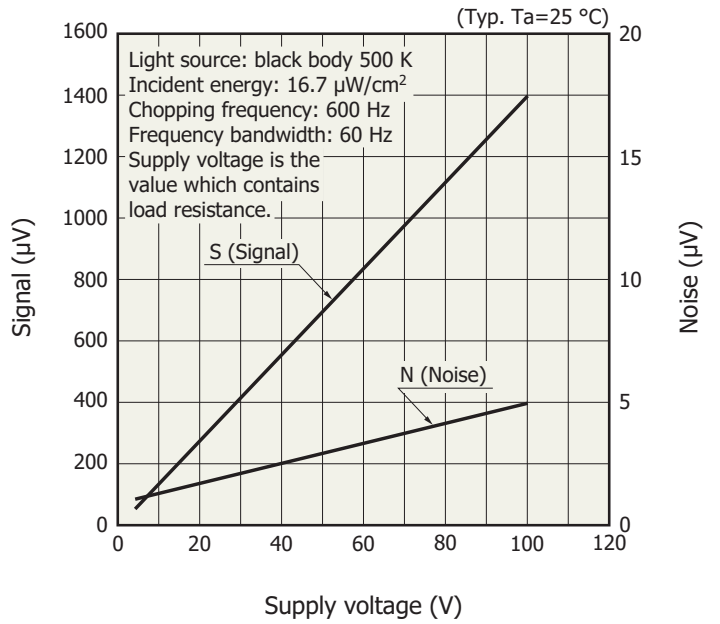
KIRD80540EB

Spectral transmittance of window material



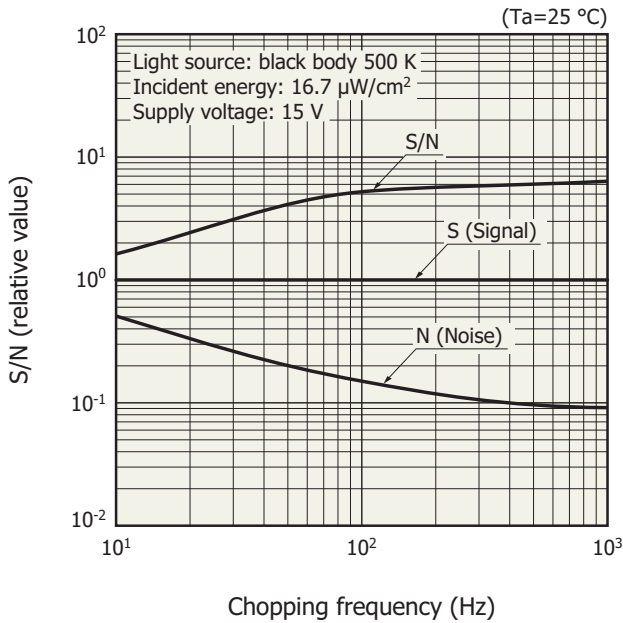
KIRDB0550EA

S/N vs. supply voltage (P9696-02)



KIRDB0547EA

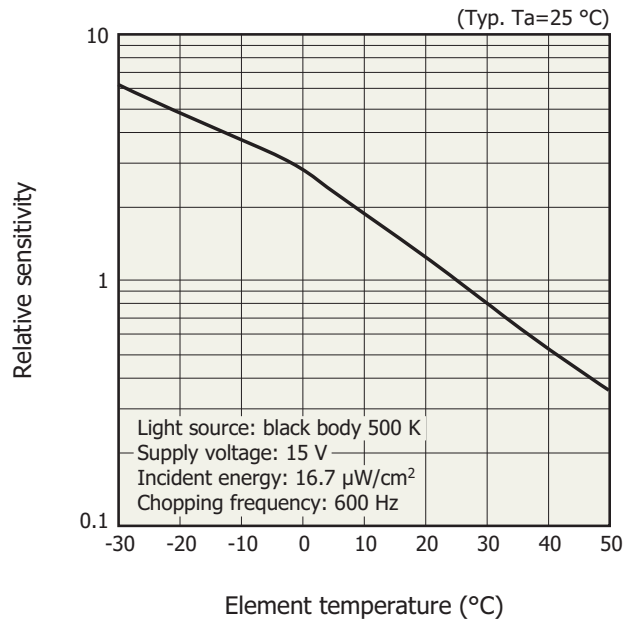
S/N vs. chopping frequency



KIRDB0441EB

Increasing the chopping frequency reduces the 1/f noise and results in an S/N improvement. The S/N can also be improved by narrowing the noise bandwidth using a lock-in amplifier.

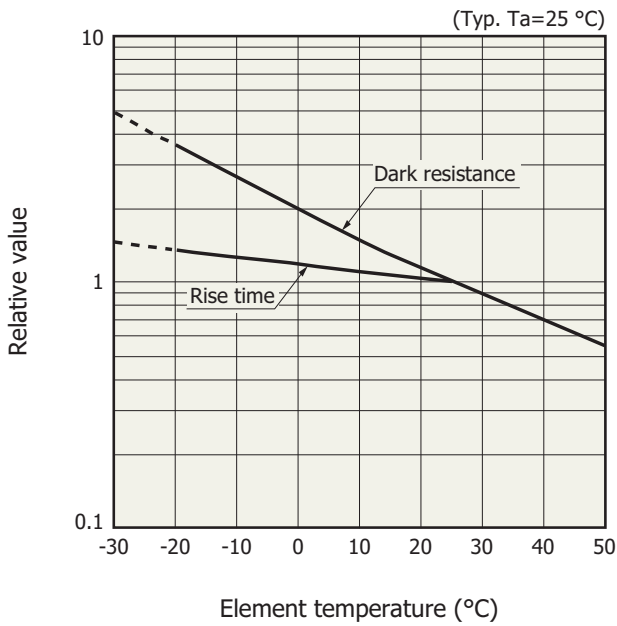
Photosensitivity vs. element temperature



KIRDB0442EC

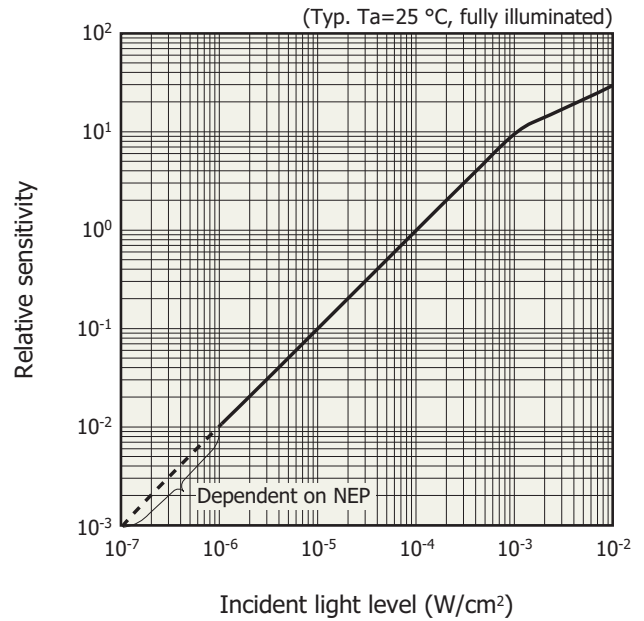
Cooling the device enhances its sensitivity, but the sensitivity also depends on the load resistance in the circuit.

Dark resistance, rise time vs. element temperature



KIRD80443EC

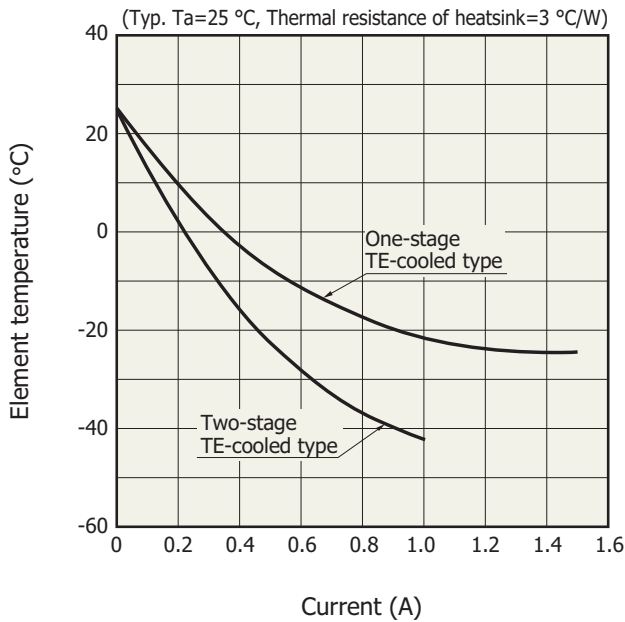
Linearity



KIRD80056EA

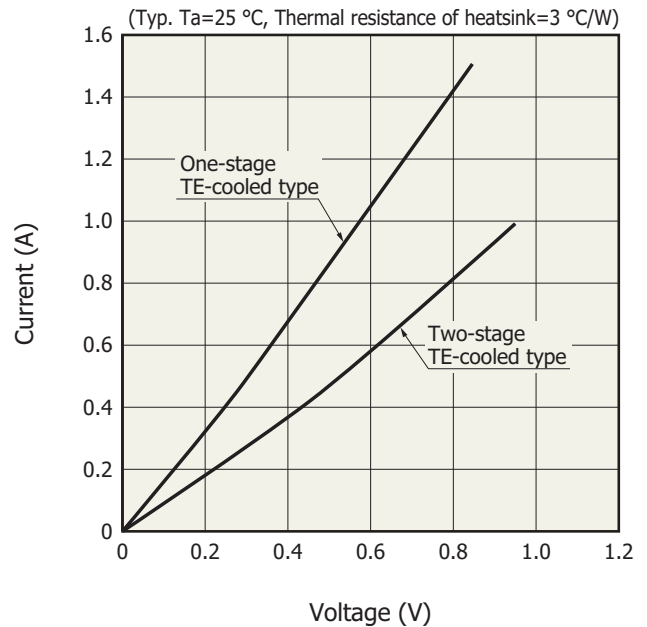
By making the incident light spot smaller than the photosensitive area, the upper limit of the linearity becomes lower.

Cooling characteristics of TE-cooler



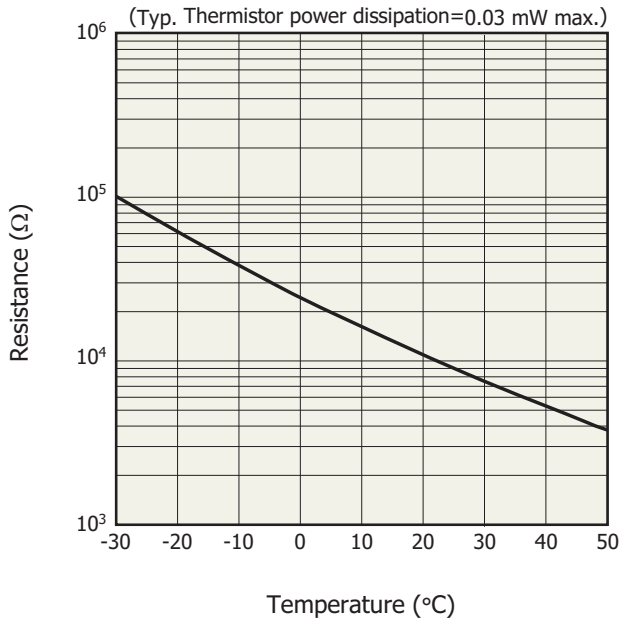
KIRD80185EB

Current vs. voltage characteristics of TE-cooler



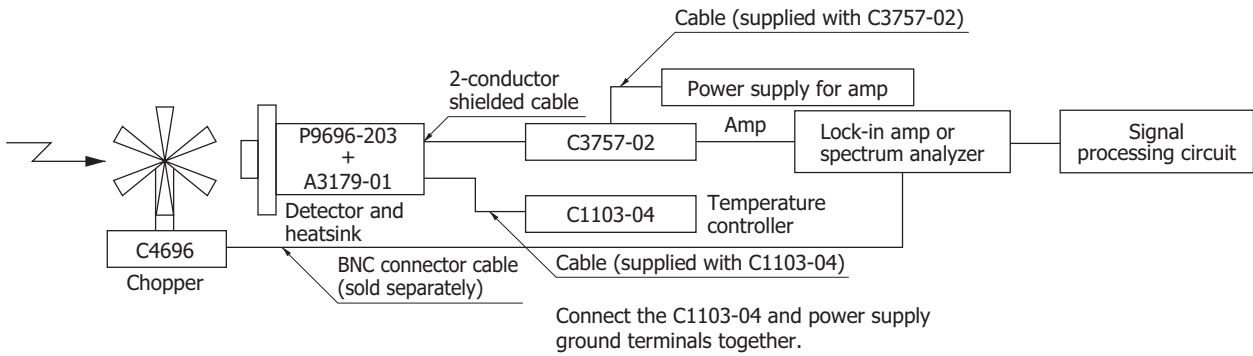
KIRD80115EC

Thermistor temperature characteristics



KIRDB0546EA

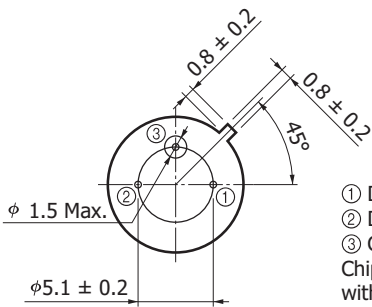
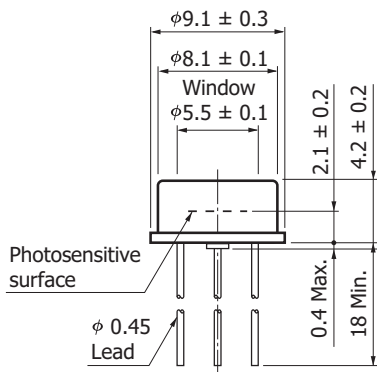
Connection example (P9696-203)



KIRDC0093EA

Dimensional outlines (unit: mm)

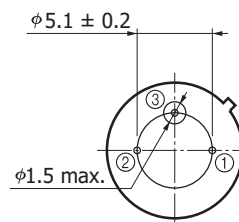
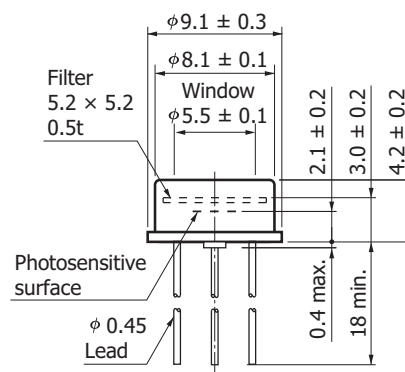
(1) P9696-02/-03



- ① Detector
 - ② Detector
 - ③ GND
- Chip position accuracy with respect to cap center 0.2 mm max.

KIRDA0183EB

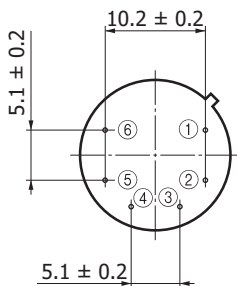
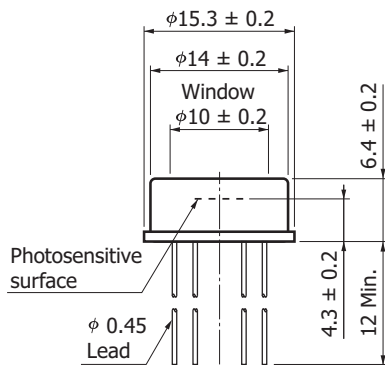
(2) P3207-08



- ① Detector
 - ② Detector
 - ③ GND
- Chip position accuracy with respect to cap center 0.2 mm max.

KIRDA0230EA

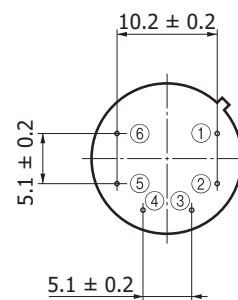
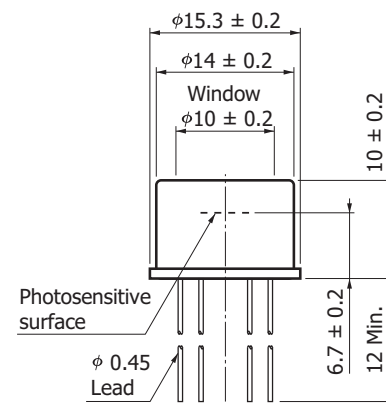
(3) P9696-102/-103



- ① Detector
 - ② Detector
 - ③ TE-cooler (-)
 - ④ TE-cooler (+)
 - ⑤ ⑥ Thermistor
- Chip position accuracy with respect to cap center 0.3 mm max.

KIRDA0128EB

(4) P9696-202/-203



- ① Detector
 - ② Detector
 - ③ TE-cooler (-)
 - ④ TE-cooler (+)
 - ⑤ ⑥ Thermistor
- Chip position accuracy with respect to cap center 0.3 mm max.

KIRDA0125EB

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

■ Precautions

- Notice
- Metal, ceramic, Plastic products/Precautions

■ Technical information

- infrared detector/technical information

Information described in this material is current as of July, 2013.

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The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use.

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